## 1. General description

PNP high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT60415NY

### 2. Features and benefits

- · High thermal power dissipation capability
- High temperature applications up to 175 °C
- Reduced Printed Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified.

# 3. Applications

- · Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Motor drive
- Relay replacement

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-40	V
I <sub>C</sub>	collector current		-	-	-15	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	-30	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -15 A; $I_B$ = -1.5 A; $t_p \le 300 \ \mu s$ ; pulsed; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	25	57	mΩ



# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	mb	C -
2	Е	emitter	<u> </u>	В
3	Е	emitter	a	, M
4	В	base		É sym132
mb	С	collector	1 2 3 4	<b>y</b> .
			LFPAK56; Power- SO8 (SOT669)	

# 6. Ordering information

#### **Table 3. Ordering information**

Type number Package					
	Name	Description	Version		
PHPT60415PY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PHPT60415PY	0415PAB

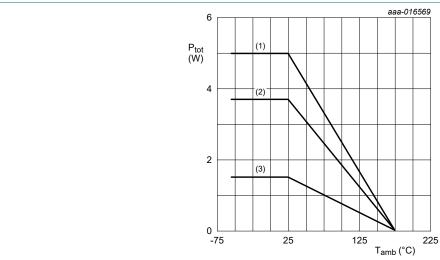
# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	-40	V
$V_{CEO}$	collector-emitter voltage	open base		-	-40	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-8	V
I <sub>C</sub>	collector current			-	-15	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-30	А
I <sub>B</sub>	base current			-	-1.5	А
I <sub>BM</sub>	peak base current	pulsed; t <sub>p</sub> ≤ 1 ms		-	-3	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	1.5	W
			[2]	-	3.7	W
			[3]	-	5	W
			[4]	-	25	W
Tj	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [4] Power dissipation from junction to mounting base.



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

40 V, 15 A PNP high power bipolar transistor

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance f junction to ambient	thermal resistance from		[1]	-	-	100	K/W
	junction to ambient		[2]	-	-	41	K/W
			[3]	-	-	30	K/W
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base			-	-	6	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

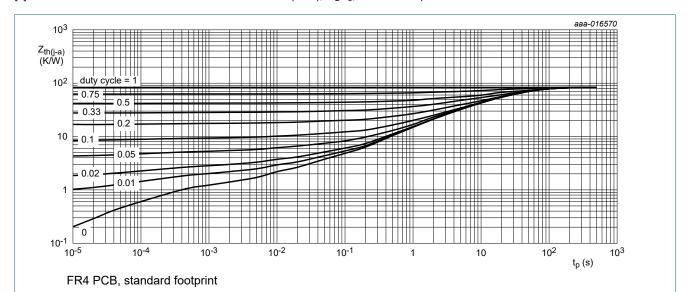


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

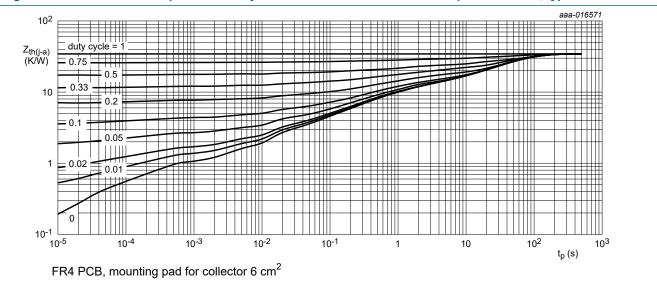


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub> collector-	collector-base cut-off	V <sub>CB</sub> = -32 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -32 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -32 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -8 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -500 mA; T <sub>amb</sub> = 25 °C	200	340	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C; pulsed	200	330	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -10 A; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C; pulsed	60	90	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -15 A; $t_{p}$ ≤ 300 μs; pulsed; δ ≤ 0.02; $T_{amb}$ = 25 °C	30	45	-	
V <sub>CEsat</sub> collector-emitter saturation voltage		$I_C$ = -1 A; $I_B$ = -50 mA; $t_p \le 300$ μs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-35	-65	mV
		$I_C$ = -10 A; $I_B$ = -1 A; $t_p \le 300 \ \mu s$ ; pulsed; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-235	-550	mV
		$I_C = -15 \text{ A}; I_B = -1.5 \text{ A}; t_p \le 300  \mu\text{s};$	-	-375	-850	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	pulsed; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	25	57	mΩ
$V_{BEsat}$	base-emitter saturation voltage	$I_C$ = -1 A; $I_B$ = -50 mA; $t_p \le 300 \mu s$ ; pulsed; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-0.95	V
		$I_C$ = -10 A; $I_B$ = -1 A; $t_p \le 300 \mu s$ ; pulsed; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-1.3	V
		$I_C$ = -15 A; $I_B$ = -1.5 A; $t_p \le 300 \text{ μs}$ ; pulsed; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	-1.4	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; I_{C} = -500 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-0.8	V
t <sub>d</sub>	delay time	$V_{CC} = -12.5 \text{ V}; I_C = -8 \text{ A}; I_{Bon} = -250 \text{ mA};$	-	20	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = 250 mA; T <sub>amb</sub> = 25 °C	-	190	-	ns
t <sub>on</sub>	turn-on time		-	210	-	ns
t <sub>s</sub>	storage time		-	155	-	ns
t <sub>f</sub>	fall time		-	80	-	ns
t <sub>off</sub>	turn-off time		-	235	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -500 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	80	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	140	-	pF

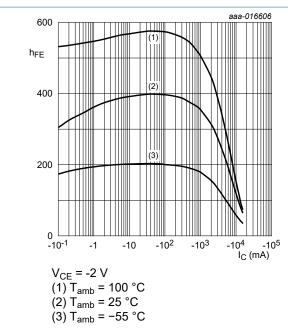


Fig. 4. DC current gain as a function of collector current; typical values

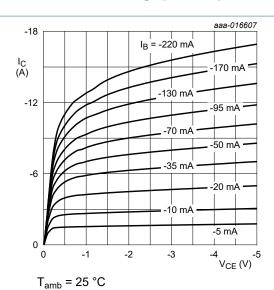
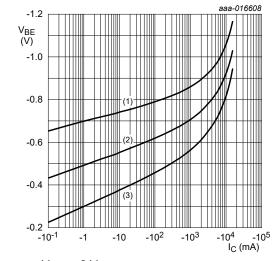


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



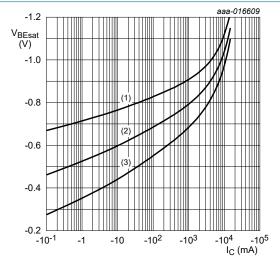
 $V_{CE} = -2 V$ 

(1)  $T_{amb} = -55$  °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 6. Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B}=20$ 

(1)  $T_{amb} = -55$  °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

#### 40 V, 15 A PNP high power bipolar transistor

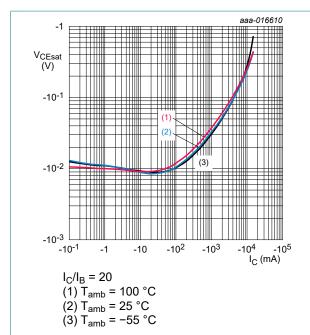


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

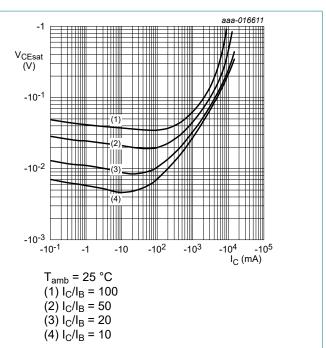


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

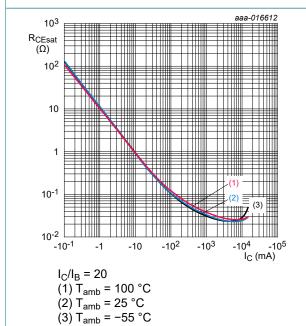


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

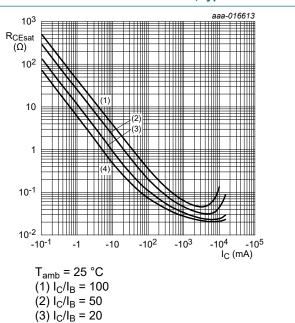
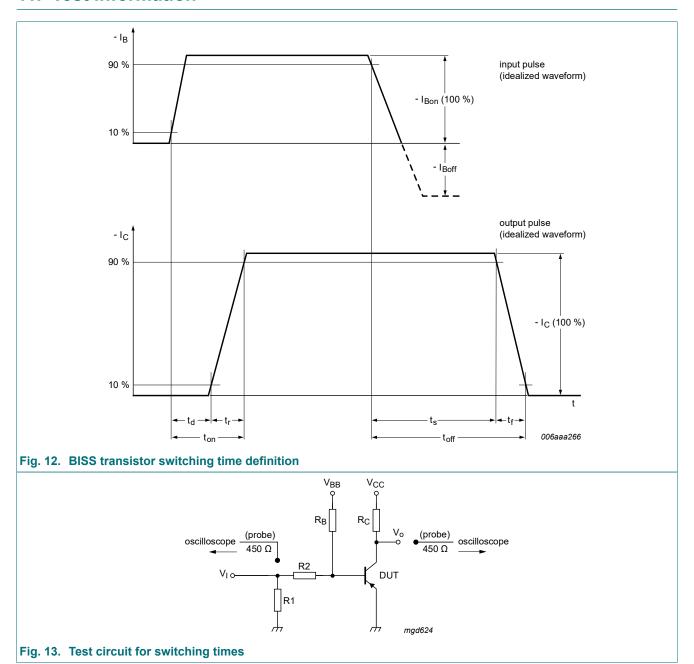


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

 $(4) I_C/I_B = 10$ 

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## 11. Test information

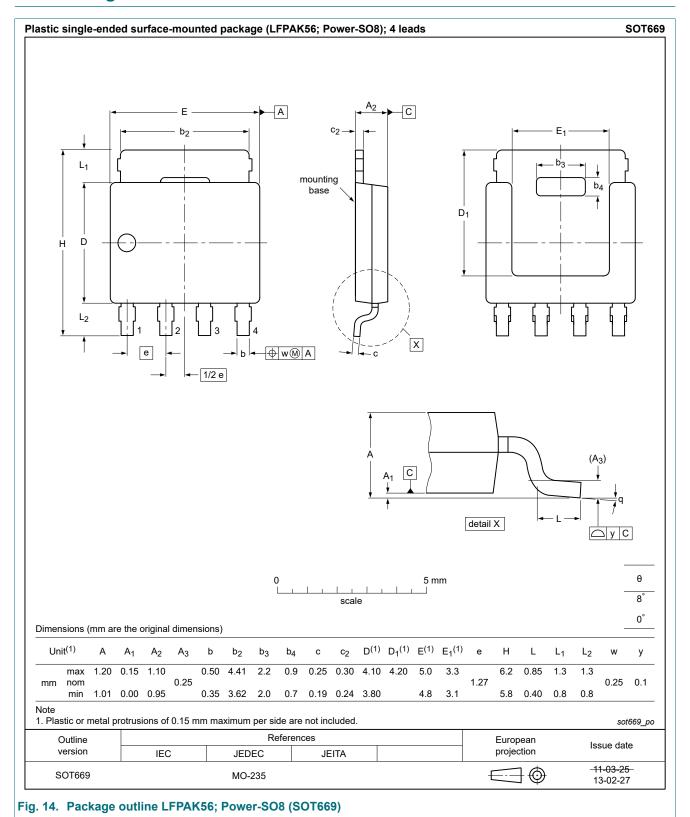


### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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# 12. Package outline

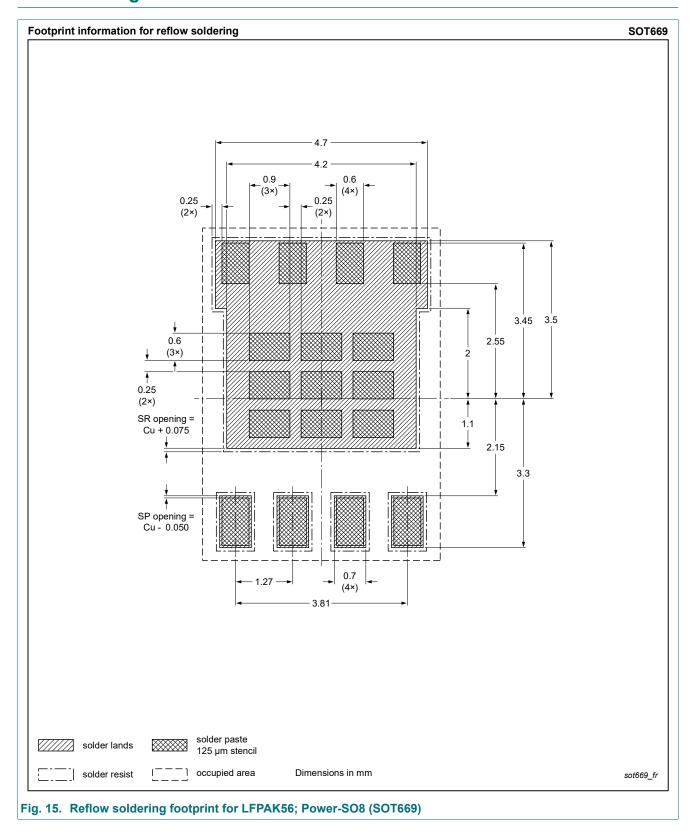


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# 13. Soldering



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# 14. Revision history

#### Table 8. Revision history

- Laboration in the contract of the contract o							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PHPT60415PY v.2	20190115	Product data sheet	-	PHPT60415PY v.1			
Modifications:	Typo at figures 2 and 3: unit corrected from ns to s at x-scale						
PHPT60415PY v.1	20150527	Product data sheet	-	-			

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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